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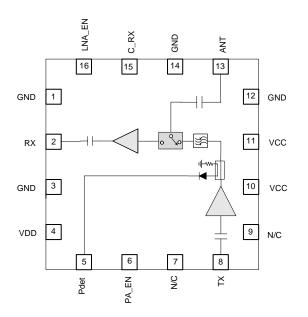
RFMD IN RFFM8500

Features

- Single Supply Voltage 3.0V to 4.8V
- Integrated 5GHz Amplifier, SPT2T TX/RX Switch, LNA, and Power Detector Coupler
- P_{OUT} = 16dBm, 11n, 54Mbps at 2% EVM

Applications

- IEEE802.11a/n WiFi Applications
- Mobile Devices
- Tablets
- Consumer Electronics
- Gaming
- Netbooks and Notebooks
- TV, Monitors, and Video



Functional Block Diagram

Product Description

The RFFM8500 provides a complete integrated solution in a single Front End Module (FEM) for WiFi 802.11a/n systems. The ultra small form factor and integrated matching minimizes the layout area in the customer's application and greatly reduces the number of external components. This simplifies the total front end solution by reducing the bill of materials, system footprint, and manufacturability cost. The RFFM8500 integrates a Power Amplifier (PA), Single Pole Double Throw switch (SP2T), LNA and a power detector coupler for improved accuracy. The device is provided in a 3mm x 3mm x 1.0mm, 16-pin laminate package. This module meets or exceeds the RF Front End needs of IEEE 802.11a/n WiFi RF systems.

RFFM8500

4.9GHz TO 5.85GHz 802.11a/n FRONT END MODULE

Package: Laminate, 16-pin, 3.0mm x 3.0mm x 1.05mm



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Absolute Maximum Ratings

5					
Parameter	Rating	Unit			
DC Supply Voltage	5.5	V _{DC}			
Maximum TX and RX Input Power (No Damage)	5	dBm			
Operating Ambient Temperature	-40 to +85	°C			
Storage Temperature	-40 to +150	°C			
Moisture Sensitivity	MSL3				



Caution! ESD sensitive device.

Caution I ESD sensitive device. Exceeding any one or a combination of the Absolute Maximum Rating conditions may cause permanent damage to the device. Extended application of Absolute Maximum Rating conditions to the device may reduce device reliability. Specified typical perfor-mance or functional operation of the device under Absolute Maximum Rating condi-tions is not implied. The information in this publication is believed to be accurate and reliable. However, no responsibility is assumed by RF Micro Devices, Inc. ("RFMD") for its use, nor for any infringement of patents, or other rights of third parties, resulting from its use. No license is granted by implication or otherwise under any patent or patent rights of RFMD, RFMD reserves the right to change component circuitry, recommended appli-cation circuitry and specifications at any time without prior notice.



RFMD Green: RoHS compliant per EU Directive 2002/95/EC, halogen free per IEC 61249-2-21, < 1000 ppm each of antimony trioxide in polymeric materials and red phosphorus as a flame retardant, and <2% antimony in added solder.

Parameter	Specification			Unit	Condition	
Farameter	Min.	Тур.	Max.	Unit	Condition	
Transmit Parameters					Nominal Operating Conditions: $V_{CC} = 3.3V$ to 4.2V; SW Control High: V_{CC} -0.2V; PA_EN = V_{CC} -0.2V; P _{OUT} =16dBm; Freq=5.18GHz to 5.825GHz; Modulation MCS7 HT20; Temp = -10°C to +70°C; Unless Otherwise Noted	
Frequency	5.15		5.85	GHz		
Power Supply V _{CC}	3	3.3	4.8	V		
Switch Control Voltage-high	2.8	3.1	4.6	V		
Switch Control Voltage-Low		0	0.2	V		
PA_EN						
ON	2.8	3.1	4.6	V	PA_EN tracks with $V_{CC}.$ Do not use PA_EN hgher than $V_{CC}.$	
OFF		0	0.2	V		
Gain	24	26		dB	V_{CC} = 3.3V; Temp = 25°C; Freq = 5.18GHz to 5.35GHz	
	26	28		dB	V _{CC} = 3.3V; Temp = 25°C; Freq = 5.35GHz to 5.825GHz	
	23	27		dB		
Dynamic EVM		2	2.5	%	V _{CC} = 3.3V; Temp = 25°C	
		2	2.5	%	P _{OUT} = 15.5dBm	
Quiescent Current		185		mA	RF off; V _{CC} = 3.3V; Temp = 25°C	
		185	210	mA	RF off	
Operating Current		230	245	mA	V _{CC} = 3.3V; Temp = 25°C	
		230	260	mA		
PAEN Current		35	50	μΑ		
FEM Leakage Current		2	10	μΑ	RF off; PAEN = OFF ; V _{CC} = "ON"	
Second Harmonic		-45	-35	dBm	Fo = 4.9GHz to 5.3GHz: P _{OUT} = 18dBm; RBW = 1MHz	
			-43	dBm	Fo = 5.3GHz and 5.85GHz: P _{OUT} = 18dBm; RBW = 1MHz	
Third Harmonic		-50	-43	dBm	Fo = 5.15GHz to 5.85GHz: P _{OUT} = 18dBm; RBW = 1MHz	
Power Detector						
P _{OUT} at OdBm	350	375	400	mV		
P _{OUT} at 16dBm	500	600	700	mV		
TX Port Return Loss	9.6	15		dB	at TX input	
ANT Port Return Loss	10	15		dB	in TX mode	
PA Switching Time- V _{REF} (on<->off)		200	600	nS		
PA Stability					Unconditional into 4:1 VSWR, No spurious above - 41.25dBm/MHz	

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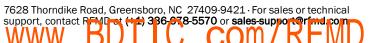
RFFM8500

Parameter	Specification			Unit	Condition
Farameter	Min.	Тур.	Max.	Unit	Condition
Receive Parameters					Operating Conditions: V_{DD} = 3.3V to 4.2V; SW Control High: V_{DD} -0.2V; LNA_EN = 2.8V to 4.2V; Freq=5.18GHz to 5.825GHz; Temp = -10°C to +70°C; Unless Otherwise Noted
Frequency	5.15		5.85	GHz	
LNA Voltage Supply (V _{DD})	3	3.3	4.8	V	
LNA_EN Voltage	2.8	3.1	4.6	V	
Gain	13	15	16	dB	Temp=25°C; V _{DD} =3.3v
	11	15	17	dB	
NF		2.5	2.8	dB	Temp=25°C; V _{DD} = 3.3V
		2.5	3.7	dB	
Rx Port Return Loss	8	15		dB	
ANT Port Return Loss	6	8		dBm	
Input IP3		-3		dBm	
Input P1dB		-13		dBm	
I _{DD}		13	17	mA	
LNAEn Control Current		30	100	μΑ	
LNA Turn On Time		200	600	nS	
Isolation					
TX-RX	32			dB	Measured from ANT to RX while in Tx mode
Switch Control Current - Each Line		0.5	1	μΑ	
Switching Speed			100	nS	
ESD					
Human Body Model (HBM)	500			V	EIA/JESD22-114A RF pins
	1000			V	EIA/JESD22-114A DC pins
Charge Device Model	1000			V	JESD22-C101C

Logic Control Table

Mode	PA_EN	LNA_EN	C_RX
Standby	Low	Low	Low
802.11a/n TX	High	Low	Low
802.11a/n RX Gain	Low	High	High

Pin	Function	Description
1	GND	Ground connection.
2	RX	RF output port for the 802.11a/n LNA. Input is matched to 50Ω and DC block is provided.
3	GND	Ground connection.
4	VDD	Supply voltage for the LNA. See applications schematic for biasing and bypassing components.
5	PDET	Power detector voltage for TX section. PDET voltage varies with output power. May need external capacitor for noise decoupling.
6	PA_EN	Control voltage for the PA and TX switch. See truth table for proper settings.
7	NC	Not connected.
8	ТХ	RF input port for the 802.11a/n PA. Input is matched to 50Ω and DC block is provided.
9	NC	Not connected.
10	VCC	Supply voltage for the PA. See applications schematic for biasing and bypassing components.
11	VCC	Supply voltage for the PA. See applications schematic for biasing and bypassing components.
12	GND	Ground connection.
13	ANT	RF bidirectional antenna port matched to 50Ω and is DC blocked internally.
14	GND	Ground connection.
15	C_RX	Receive switch control pin. See switch truth table for proper level.
16	LNA_EN	Control voltage for the LNA.
Pkg Base	GND	Ground connection.

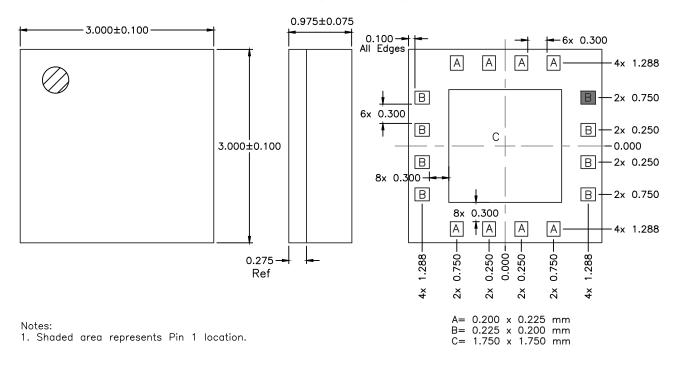


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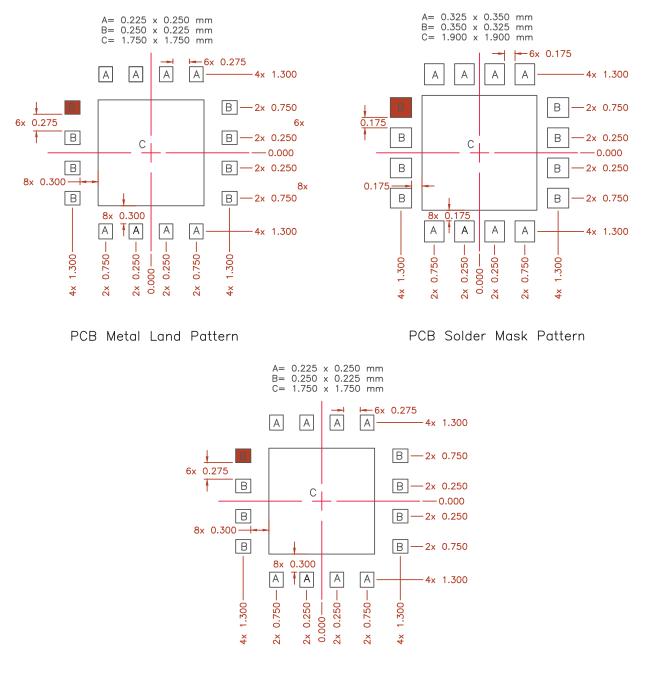


Package Drawing





PCB Patterns

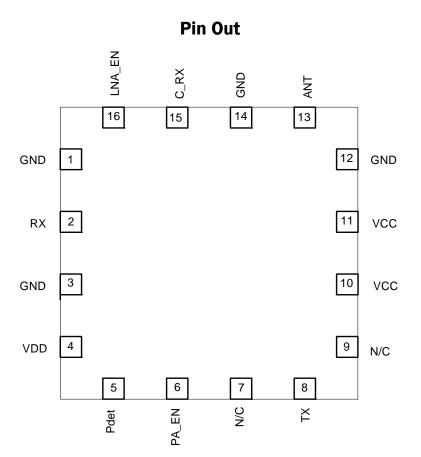


PCB Stencil Pattern

Notes:

- 1. Shaded area represents Pin 1 location.
- 2. Thermal vias for center slug "C" should be incorporated into the PCB design. The number and size of thermal vias will depend on the application, power dissipation and electrical requirements. Example of the number and size of vias can be found on the RFMD evaluation board layout (gerber files are available upon request).

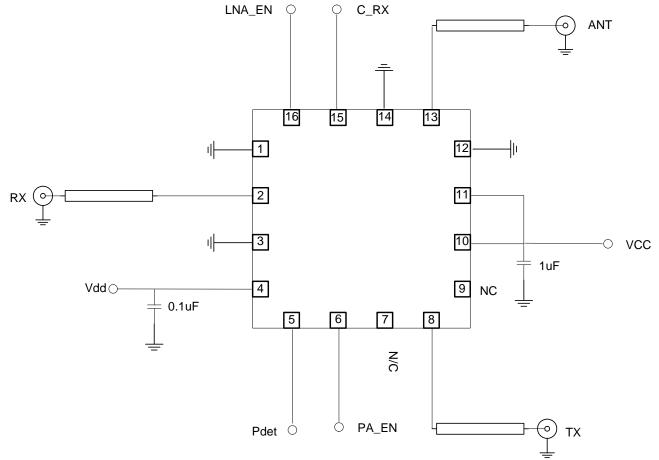








Applications Schematic



Note:

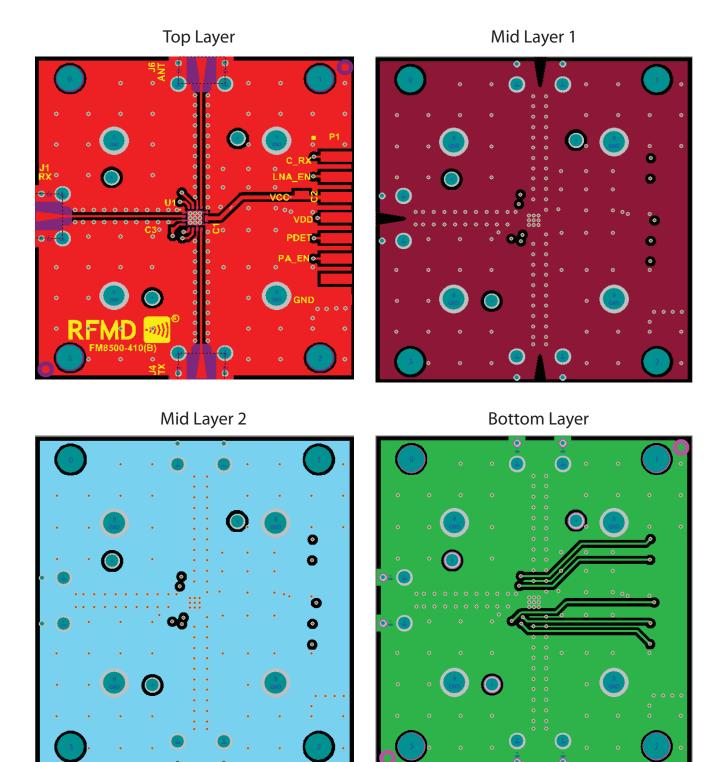
1. Pins 1, 3, 7, 9, 12, and 14 are not connected internally. These pins can be left floating or grounded. It is recommended to follow the RFMD evaluation board layout.

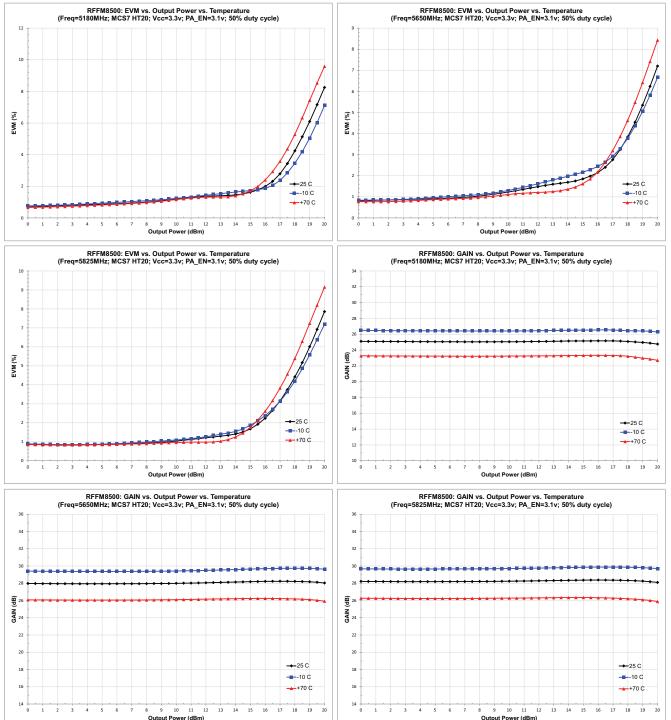






RFFM8500 Evaluation Board Layers





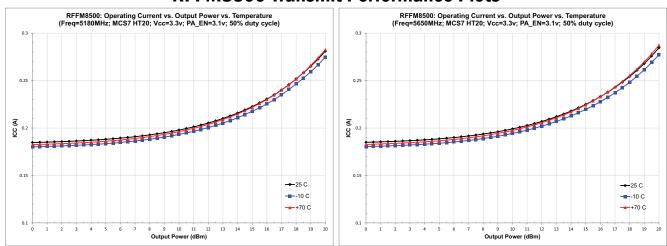
RFFM8500 Transmit Performance Plots

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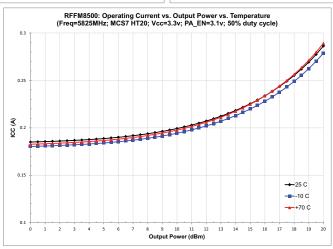
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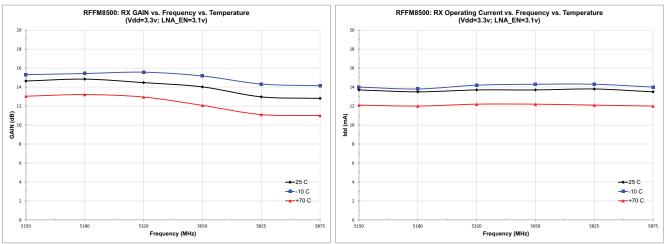




RFFM8500 Transmit Performance Plots



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RFFM8500 Receive Performance Plots

